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- SiC-based extreme ultraviolet (EUV) photodiode
- Excellent stability under high fluence EUV exposure
- Photovoltaic mode operation
- Visible blind and low dark current
- Windowless TO-8 metal housing
- High detection efficiency for 13.5 nm EUV radiation

EUV radiation monitoring and flux measurement

Operation temperature range	$T_{opt}$	-20-80	°C
Storage temperature range	$T_{sto}$	-55-90	°C
Soldering temperature (3 s)	$T_{sol}$	260	°C
Maxium reverse voltage	$V_{r-max}$	-20	V

Chip size

# áres